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Kind regards,

Team Nexperia

PDTD123E series

NPN 500 mA, 50 V resistor-equipped transistors;

R1 = 2.2 k Ω , R2 = 2.2 k Ω

Rev. 02 — 16 November 2009

Product data sheet

1. Product profile

1.1 General description

500 mA NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package			PNP complement
	NXP	JEITA	JEDEC	
PDTD123EK	SOT346	SC-59A	TO-236	PDTB123EK
PDTD123ES ^[1]	SOT54	SC-43A	TO-92	PDTB123ES
PDTD123ET	SOT23	-	TO-236AB	PDTB123ET

[1] Also available in SOT54A and SOT54 variant packages (see [Section 2](#)).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs
- ± 10 % resistor ratio tolerance

1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs
- Cost saving alternative for BC817 series in digital applications
- Switching loads

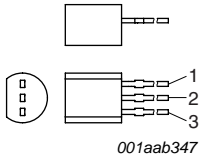
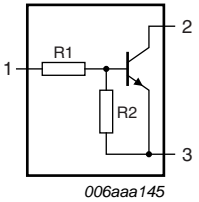
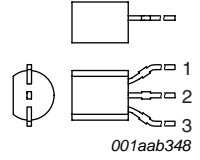
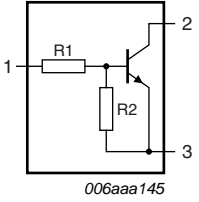
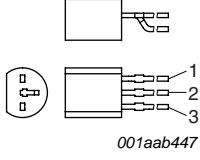
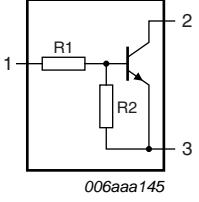
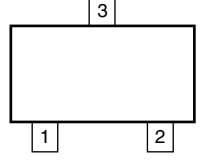
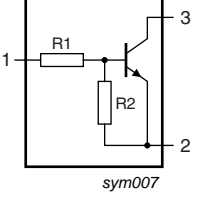
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		0.9	1.0	1.1	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)	 <p>001aab347</p>	 <p>006aaa145</p>
2	output (collector)		
3	GND (emitter)		
SOT54A			
1	input (base)	 <p>001aab348</p>	 <p>006aaa145</p>
2	output (collector)		
3	GND (emitter)		
SOT54 variant			
1	input (base)	 <p>001aab447</p>	 <p>006aaa145</p>
2	output (collector)		
3	GND (emitter)		
SOT23, SOT346			
1	input (base)	 <p>006aaa144</p>	 <p>sym007</p>
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTD123EK	SC-59A	plastic surface mounted package; 3 leads	SOT346
PDTD123ES ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTD123ET	-	plastic surface mounted package; 3 leads	SOT23

[1] Also available in SOT54A and SOT54 variant packages (see [Section 2](#) and [Section 9](#)).

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTD123EK	E3
PDTD123ES	D123ES
PDTD123ET	*7T

[1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
V_I	input voltage				
	positive		-	+12	V
	negative		-	-10	V
I_O	output current (DC)		-	500	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	^[1]		
	SOT346		-	250	mW
	SOT54		-	500	mW
	SOT23		-	250	mW
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$
T_{amb}	ambient temperature		-65	+150	$^\circ\text{C}$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	SOT346		-	-	500	K/W
	SOT54		-	-	250	K/W
	SOT23		-	-	500	K/W

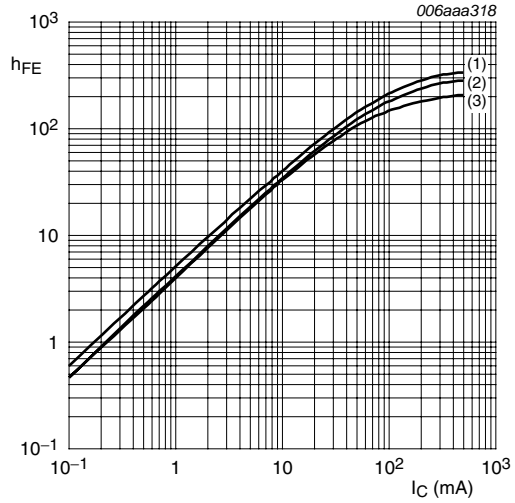
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

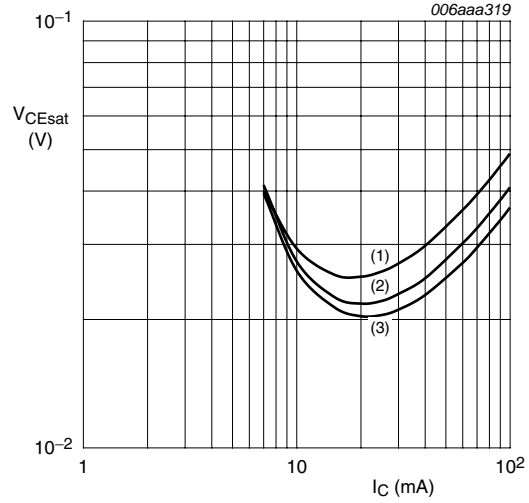
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
		$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 50\text{ V}; I_B = 0\text{ A}$	-	-	0.5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	2	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 50\text{ mA}$	40	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	-	-	0.3	V
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 100\text{ }\mu\text{A}$	0.6	1.1	1.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 20\text{ mA}$	1.0	1.5	2.0	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		0.9	1.0	1.1	
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A};$ $f = 100\text{ MHz}$	-	7	-	pF



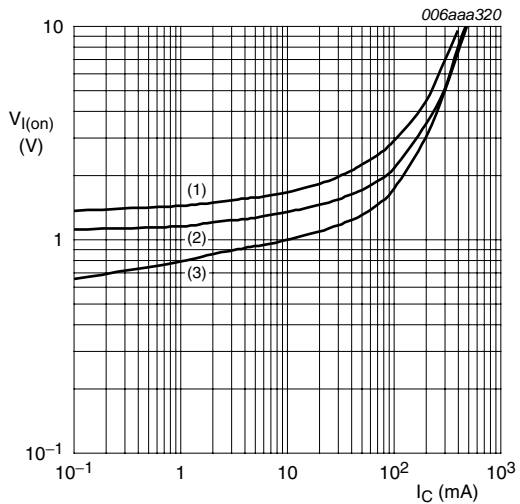
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 1. DC current gain as a function of collector current; typical values



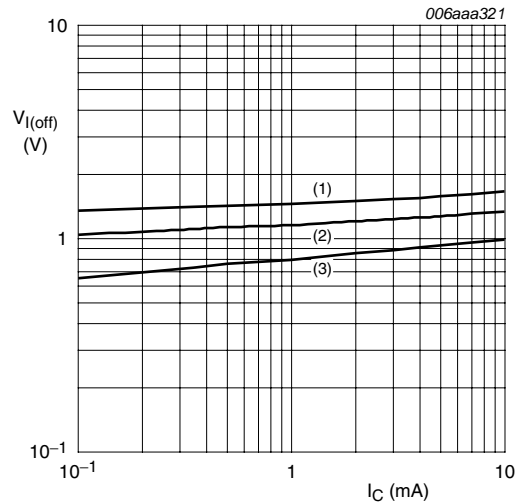
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 3. On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 4. Off-state input voltage as a function of collector current; typical values

8. Package outline

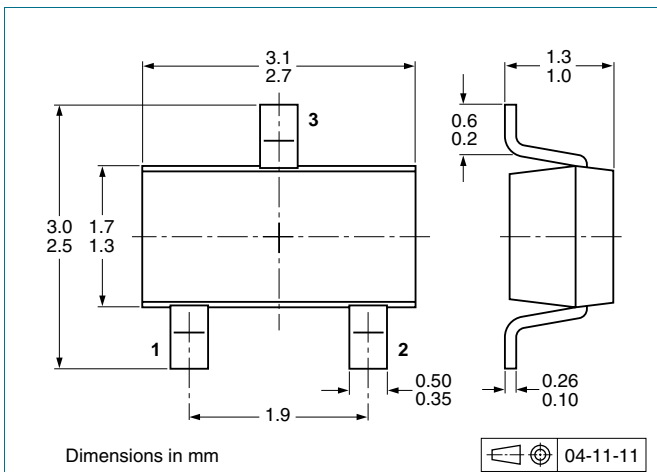


Fig 5. Package outline SOT346 (SC-59A/TO-236)

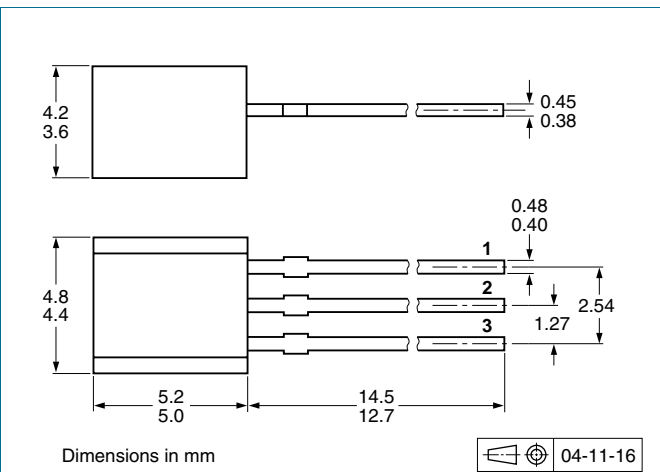


Fig 6. Package outline SOT54 (SC-43A/TO-92)

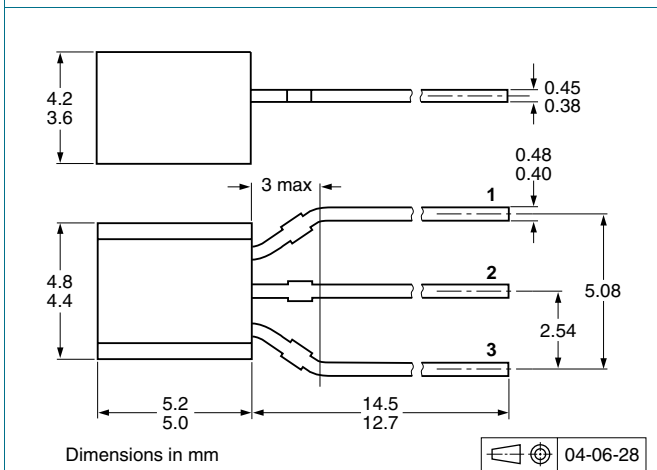


Fig 7. Package outline SOT54A

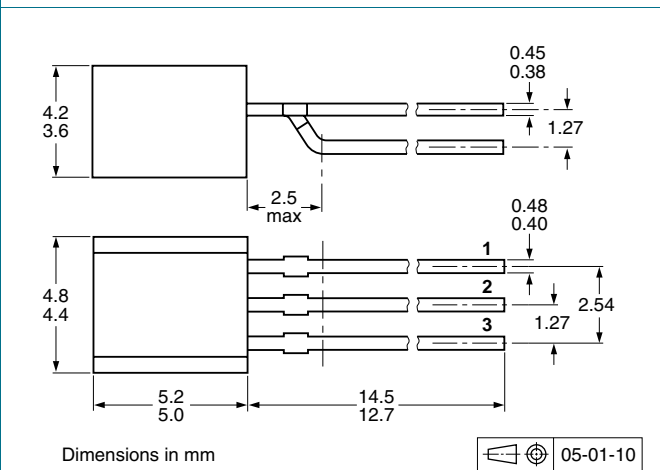


Fig 8. Package outline SOT54 variant

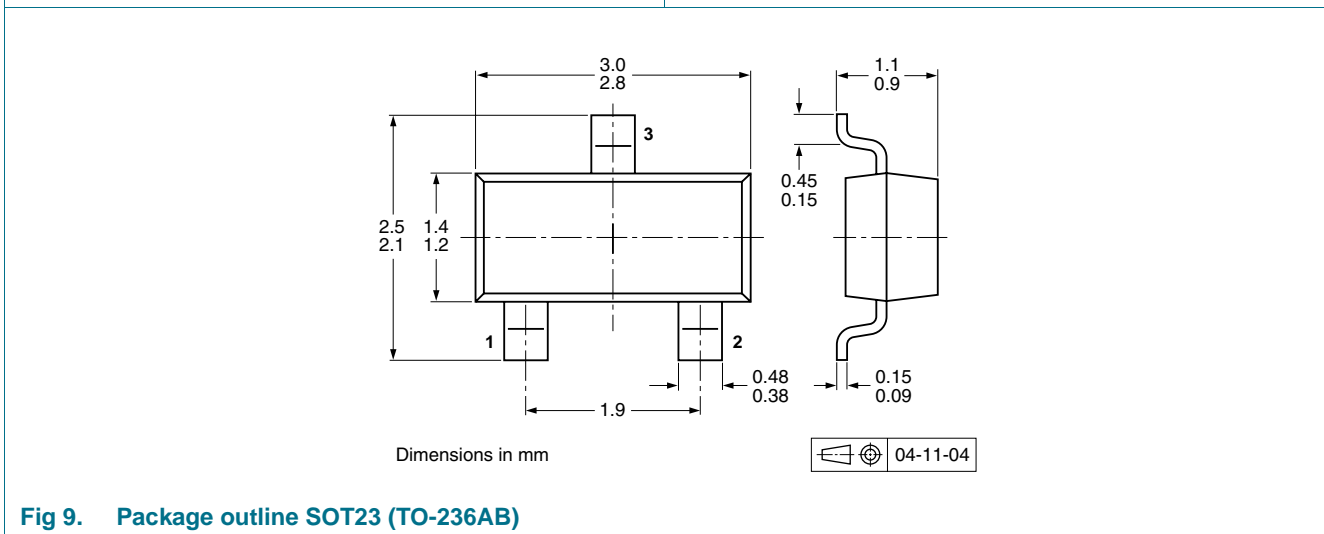


Fig 9. Package outline SOT23 (TO-236AB)

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTD123EK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTD123ES	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTD123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235

[1] For further information and the availability of packing methods, see [Section 12](#).

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD123E_SER_2	20091116	Product data sheet	-	PDTD123E_SER_1
Modifications:	<ul style="list-style-type: none">This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.			
PDTD123E_SER_1	20050408	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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